CEP04N100/CEB04N100
CEF04N100

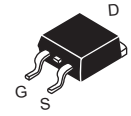
N-Channel Enhancement Mode Field Effect Transistor

PRELIMINARY

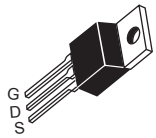
FEATURES

Type	V_{DSS}	$R_{DS(ON)}$	I_D	@V_{GS}
CEP04N100	1000V	3.8Ω	4A	10V
CEB04N100	1000V	3.8Ω	4A	10V
CEF04N100	1000V	3.8Ω	4A [d]	10V

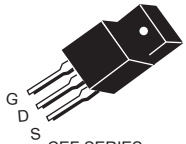
- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handing capability.
- RoHS compliant.



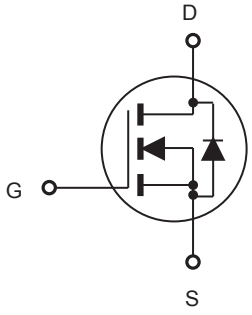
CEB SERIES
TO-263(DD-PAK)



CEP SERIES
TO-220



CEF SERIES
TO-220F



ABSOLUTE MAXIMUM RATINGS T_C = 25°C unless otherwise noted

Parameter	Symbol	Limit		Units
		TO-220/263	TO-220F	
Drain-Source Voltage	V_{DS}	1000		V
Gate-Source Voltage	V_{GS}	±30		V
Drain Current-Continuous	I_D	4	4 [d]	A
Drain Current-Pulsed [a]	I_{DM} [e]	16	16[d]	A
Maximum Power Dissipation @ T_C = 25°C	P_D	166	50	W
- Derate above 25°C		1.3	0.4	W/°C
Operating and Store Temperature Range	T_J,T_{stg}	-55 to 150		°C

Thermal Characteristics

Parameter	Symbol	Limit		Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.75	2.5	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	65	°C/W

This is preliminary information on a new product in development now .
Details are subject to change without notice .

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http://www.cet-mos.com

Electrical Characteristics T_C = 25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0V, I_D = 250μA	1000			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =1000V, V_{GS} = 0V			1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	V_{GS} = 30V, V_{DS} = 0V			100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	V_{GS} = -30V, V_{DS} = 0V			-100	nA
On Characteristics [b]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS} = V_{DS}, I_D = 250μA	2		4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 4A		3	3.8	Ω
Dynamic Characteristics [c]						
Input Capacitance	C_{iss}	V_{DS} = 25V, V_{GS} = 0V, f = 1.0 MHz		1390		pF
Output Capacitance	C_{oss}			115		pF
Reverse Transfer Capacitance	C_{rss}			15		pF
Switching Characteristics [c]						
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 300V, I_D =4A, V_{GS} = 10V, R_{GEN} = 25Ω		33		ns
Turn-On Rise Time	t_r			17		ns
Turn-Off Delay Time	$t_{d(off)}$			82		ns
Turn-Off Fall Time	t_f			25		ns
Total Gate Charge	Q_g	V_{DS} = 480V,I_D = 4A, V_{GS} = 10V		27		nC
Gate-Source Charge	Q_{gs}			7		nC
Gate-Drain Charge	Q_{gd}			7		nC
Drain-Source Diode Characteristics and Maximun Ratings						
Drain-Source Diode Forward Current	I_S [f]				4	A
Drain-Source Diode Forward Voltage [b]	V_{SD} [g]	V_{GS} = 0V, I_S = 4A			1.4	V

Notes :
a.Repetitive Rating : Pulse width limited by maximum junction temperature .
b.Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2% .
c.Guaranteed by design, not subject to production testing.
d.Limited only by maximum temperature allowed .
e.Pulse width limited by safe operating area .
f.Full package $I_{S(max)}$ = 2.2A .
g.Full package V_{SD} test condition I_S = 2.2A .

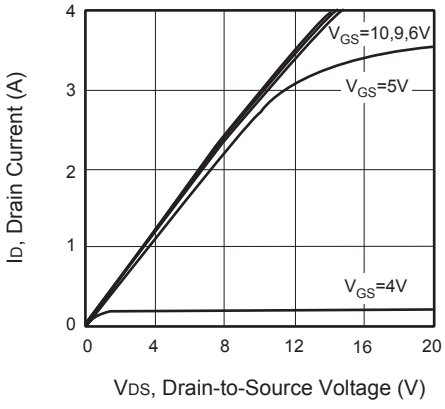

Figure 1. Output Characteristics

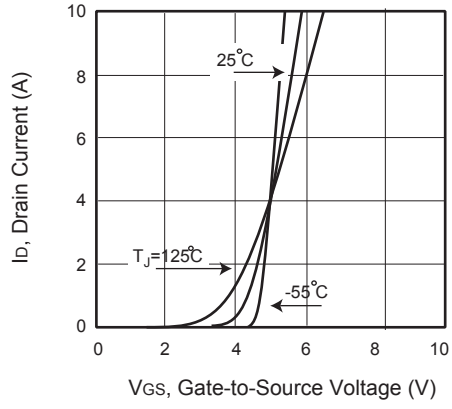

Figure 2. Transfer Characteristics

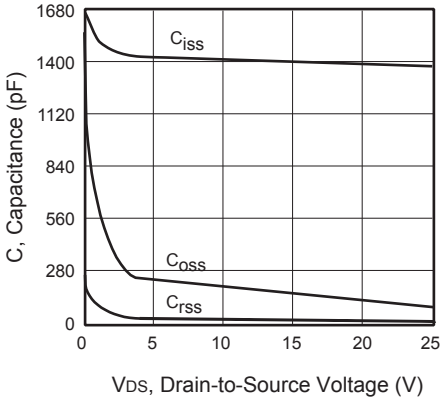

Figure 3. Capacitance

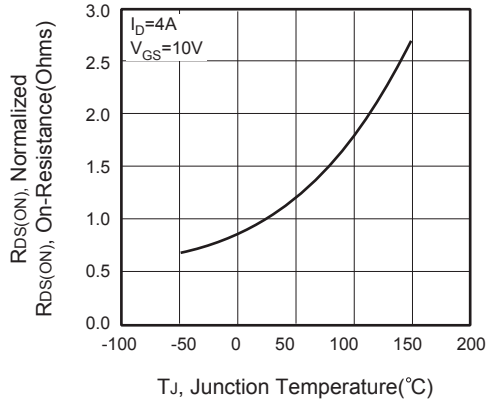

Figure 4. On-Resistance Variation with Temperature

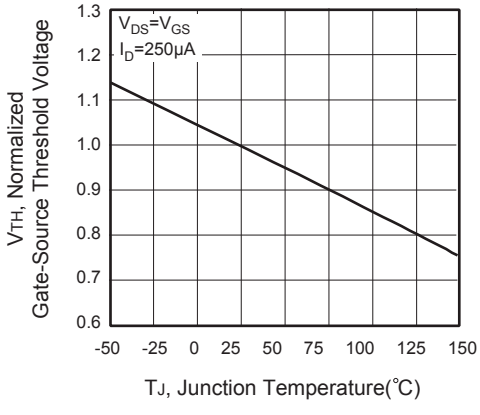

Figure 5. Gate Threshold Variation with Temperature

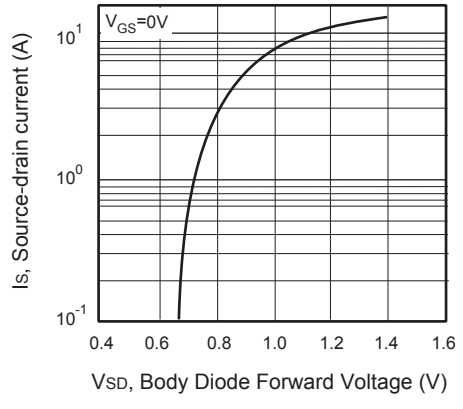

Figure 6. Body Diode Forward Voltage Variation with Source Current

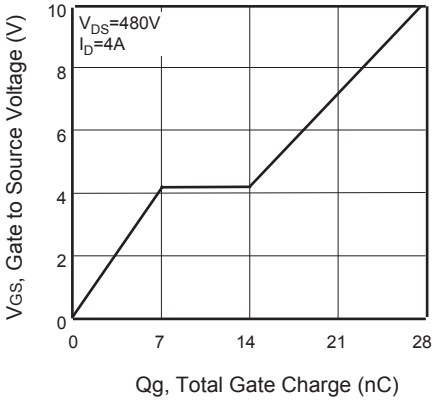

Figure 7. Gate Charge

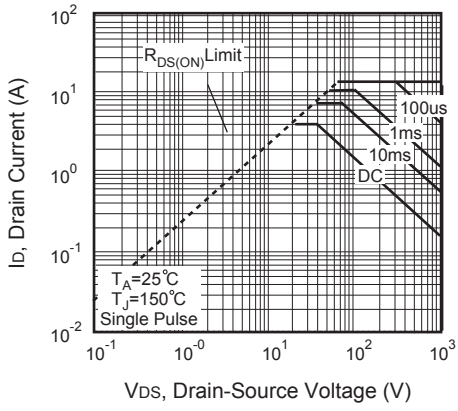

Figure 8. Maximum Safe Operating Area

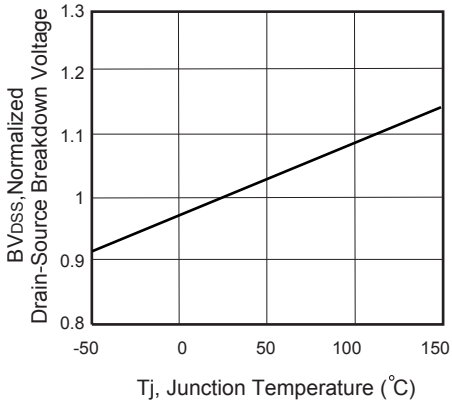

Figure 9. Breakdown Voltage Variation VS Temperature

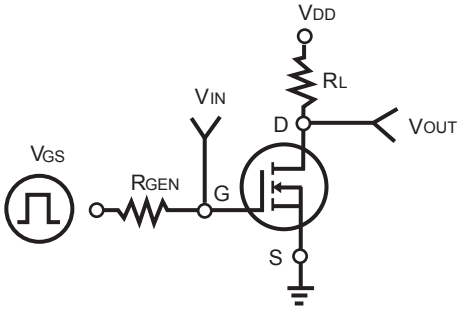

Figure 10. Switching Test Circuit

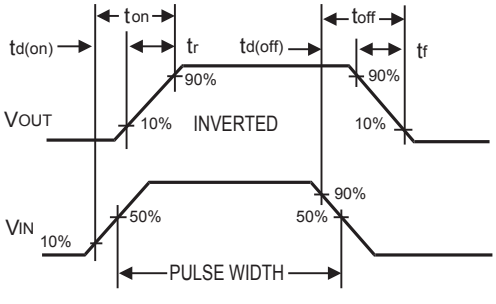

Figure 11. Switching Waveforms

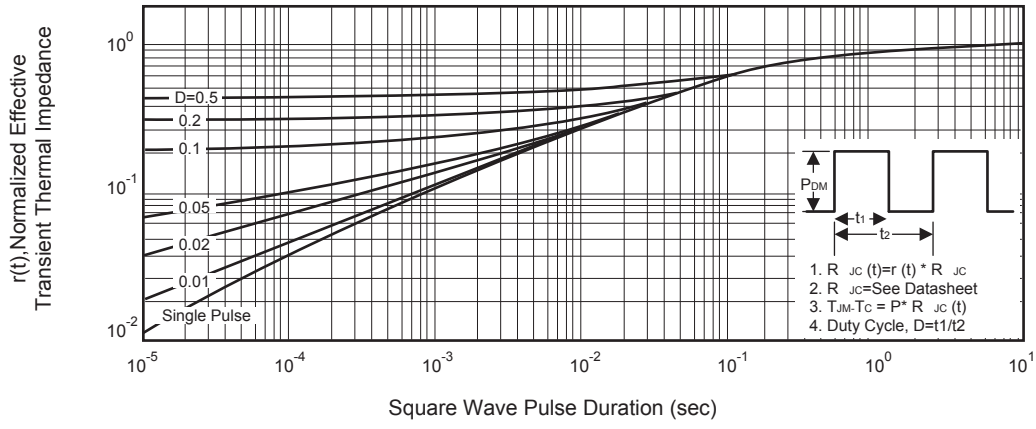

Figure 12. Normalized Thermal Transient Impedance Curve